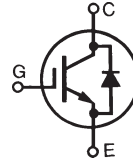


**HiPerFAST™ IGBTs**  
**B2-Class High Speed**  
**w/ Diode**

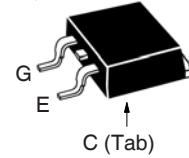
**IXGA16N60B2D1**  
**IXGP16N60B2D1**  
**IXGH16N60B2D1**

**$V_{CES} = 600V$**   
 **$I_{C110} = 16A$**   
 **$V_{CE(sat)} \leq 1.95V$**   
 **$t_{fi(typ)} = 70ns$**

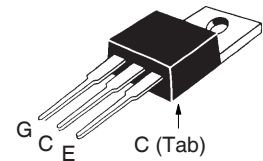


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$ (Chip Capability)	40	A
$I_{C110}$	$T_C = 110^\circ C$	16	A
$I_{F110}$	$T_C = 110^\circ C$	11	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	100	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 22\Omega$ Clamped Inductive load	$I_{CM} = 32$ $V_{CE} \leq V_{CES}$	A
$P_C$	$T_C = 25^\circ C$	150	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$M_d$	Mounting Torque (TO-220 & TO-247)	1.13/10	Nm/lb.in.
$F_C$	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6mm (0.062 in.) from Case for 10s	260	$^\circ C$
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

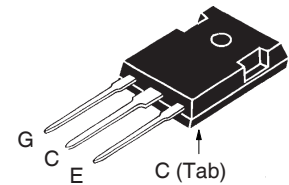
**TO-263 AA (IXGA)**



**TO-220AB (IXGP)**



**TO-247 (IXGH)**



G = Gate      C = Collector  
 E = Emitter      Tab = Collector

**Features**

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- International Standard Packages

**Advantages**

- High Power Density
- Low Gate Drive Requirement

**Applications**

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		5.5 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 1 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 12A$ , $V_{GE} = 15V$ , Note1 $T_J = 125^\circ C$		1.65	1.95 V V

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 12\text{A}, V_{CE} = 10\text{V}$ , Note 1	8		S
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		675	pF
			70	pF
			20	pF
$Q_{g(on)}$ $Q_{ge}$ $Q_{gc}$	$I_C = 12\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		24	nC
			5	nC
			13	nC
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		18	ns
			20	ns
			0.16	mJ
			73	ns
			70	ns
			0.12	0.22 mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 22\Omega$ Note 2		17	ns
			20	ns
			0.26	mJ
			140	ns
			125	ns
			0.38	mJ
$R_{thJC}$ $R_{thCK}$	TO-220 TO-247		0.83	$^\circ\text{C/W}$
		0.50	$^\circ\text{C/W}$	
		0.21	$^\circ\text{C/W}$	

### Reverse Diode (FRED)

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_F$	$I_F = 10\text{A}, V_{GE} = 0\text{V}$ , Note 1 $T_J = 125^\circ\text{C}$		1.7	3.0 V
$I_{RM}$ $t_{rr}$ $t_{rr}$	$I_F = 12\text{A}, V_{GE} = 0\text{V}$ , $-di_F/dt = 100\text{A}/\mu\text{s}, V_R = 100\text{V}, T_J = 125^\circ\text{C}$		2.5	A
			110	ns
		$I_F = 1\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 30\text{V}$		30
$R_{thJC}$				2.5 $^\circ\text{C/W}$

### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Switching times & energy losses may increase for higher  $V_{CE}(\text{Clamp})$ ,  $T_J$  or  $R_G$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.



Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

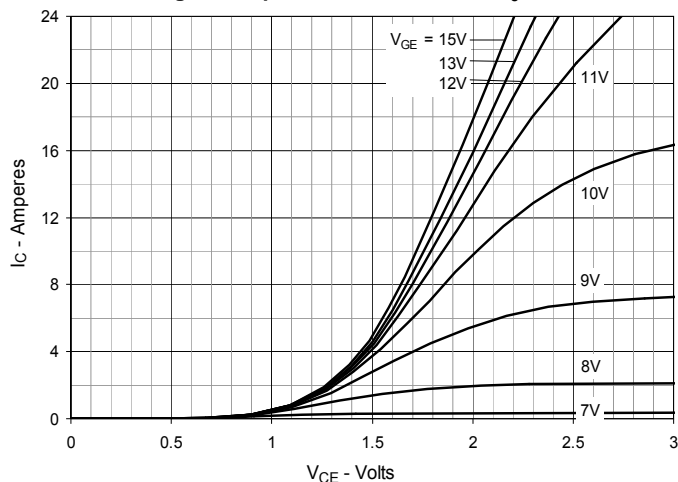


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

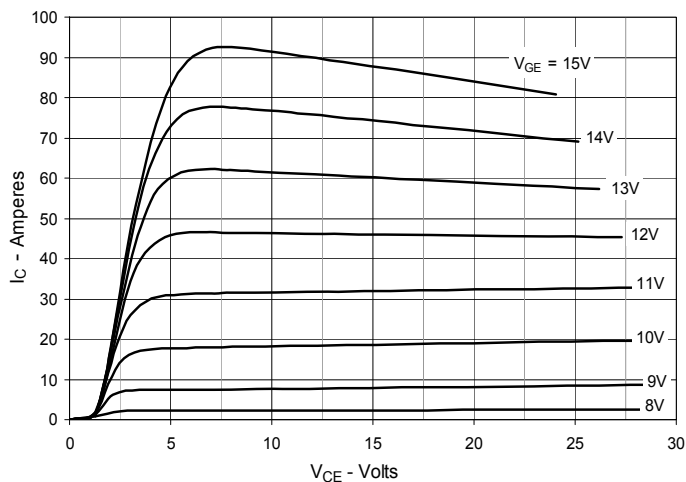


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

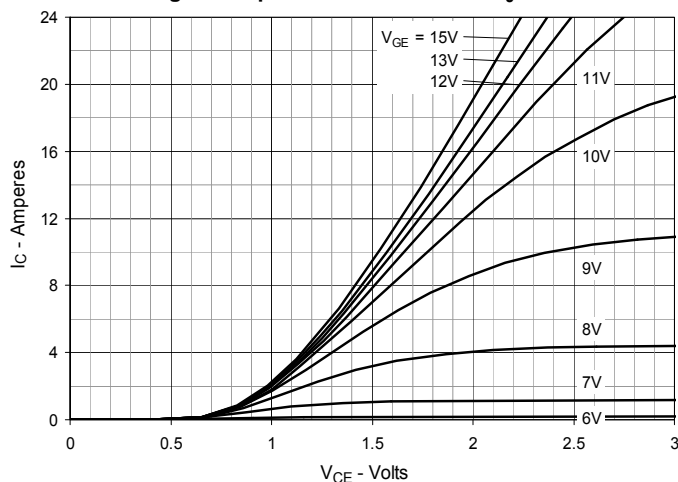


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

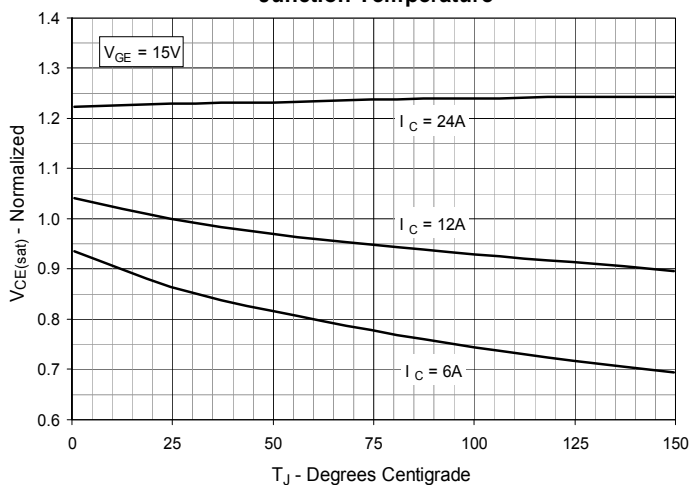


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

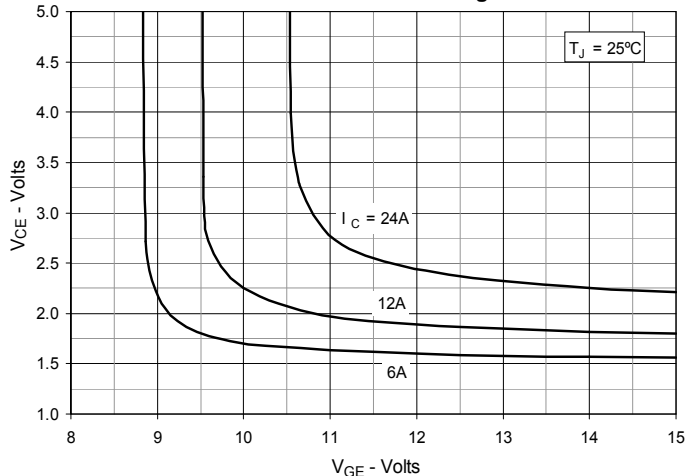


Fig. 6. Input Admittance

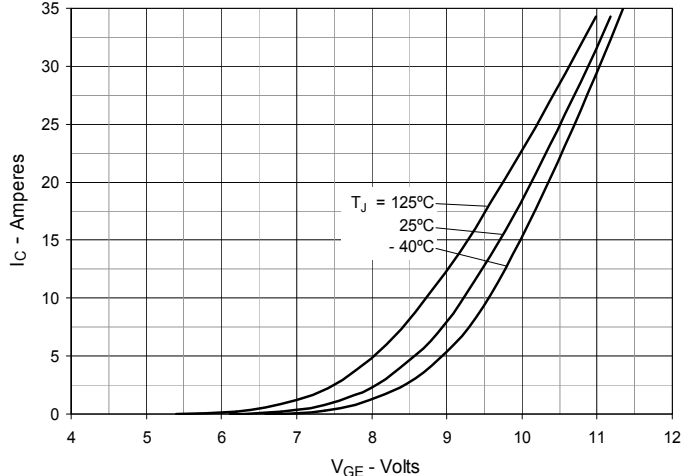


Fig. 7. Transconductance

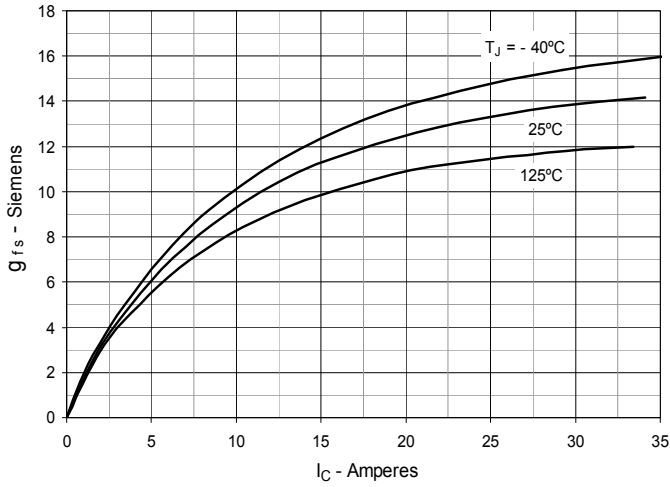


Fig. 8. Gate Charge

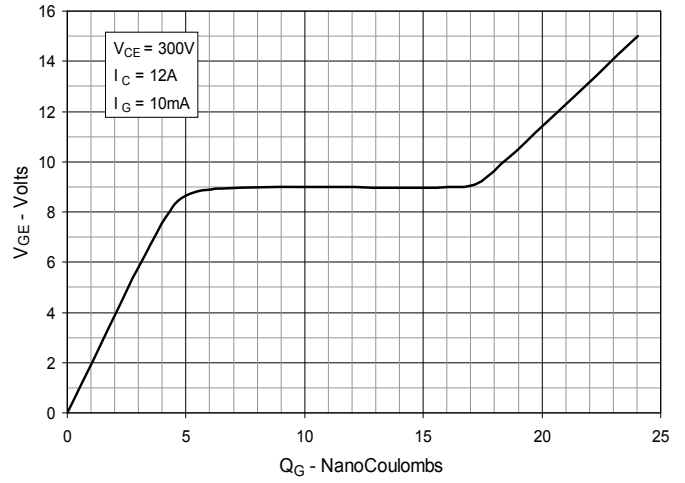


Fig. 9. Capacitance

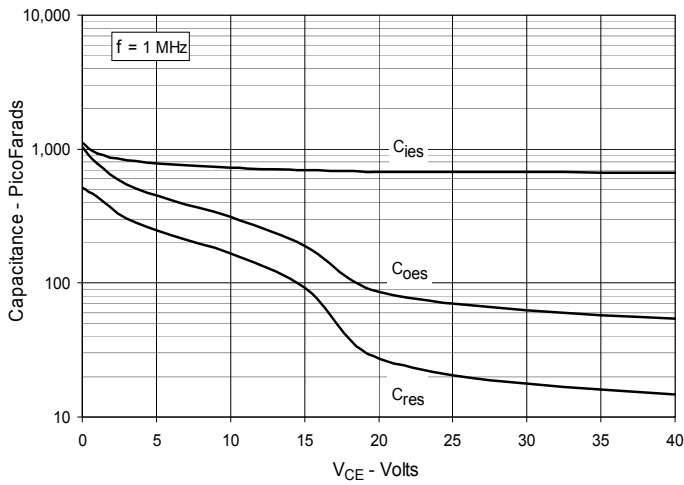


Fig. 10. Reverse-Bias Safe Operating Area

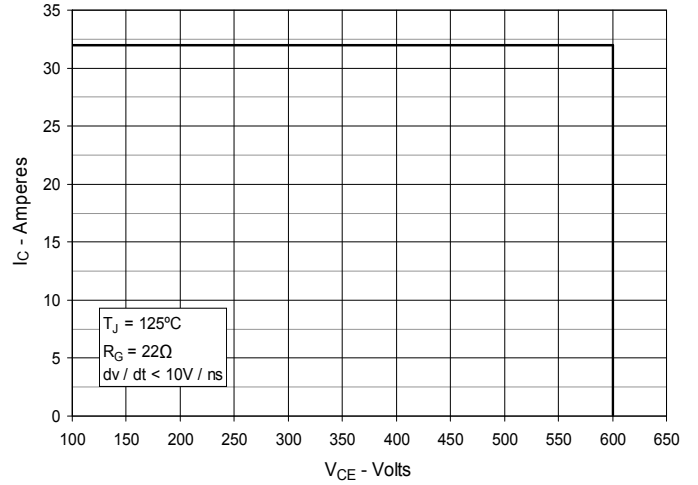
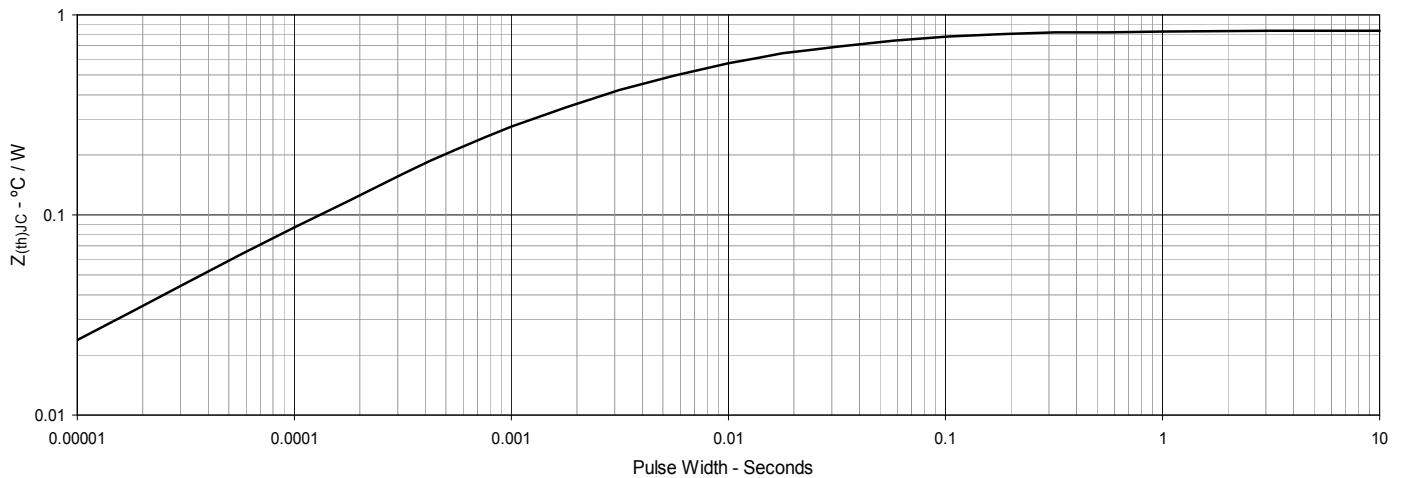
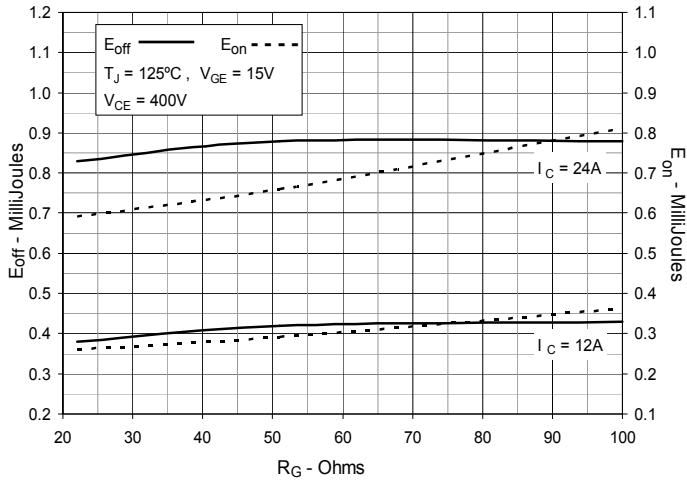


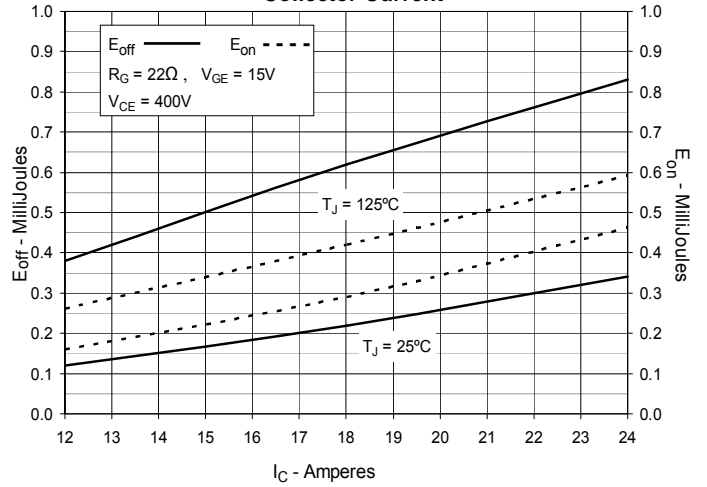
Fig. 11. Maximum Transient Thermal Impedance



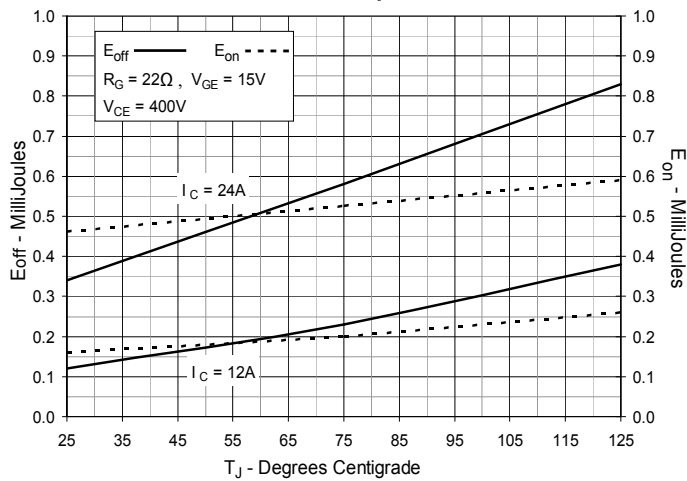
**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**



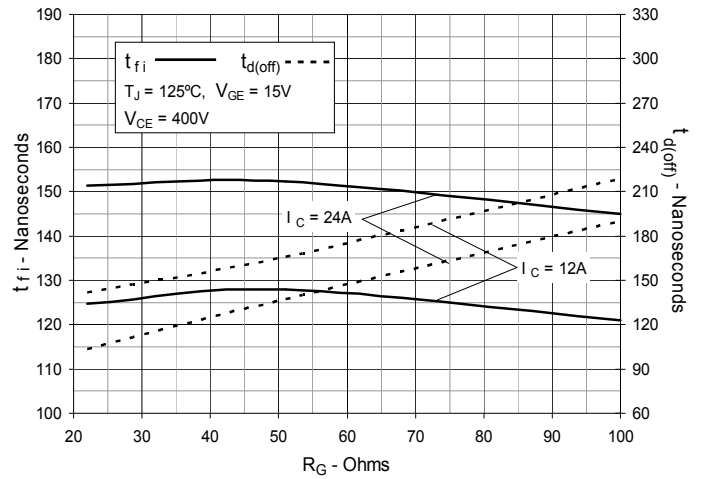
**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**



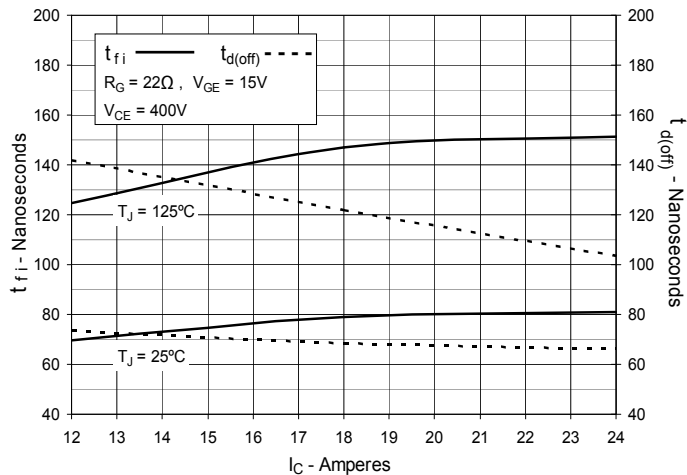
**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**



**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**



**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**



**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**

